L Number	Hits	Search Text	DB	Time stamp
8	26489	(polish or polishing or cmp or planarizing) and (etch or etching)	USPAT	2003/09/20 14:43
9	20762	((polish or polishing or cmp or planarizing) and (etch or etching)) and semiconductor	USPAT	2003/09/20 12:31
10	10204	(((polish or polishing or cmp or planarizing) and (etch or etching)) and semiconductor) and (flow or flowing)	USPAT	2003/09/20 12:32
11	1427	(((polish or polishing or cmp or planarizing) and (etch or etching)) and semiconductor) and ((flow or flowing) with (etch or etching))	USPAT	2003/09/20 13:00
12	168	((((polish or polishing or cmp or planarizing) and (etch or etching)) and semiconductor) and ((flow or flowing) with (etch or etching))) and backside	USPAT	2003/09/20 14:43
13	27	(((((polish or polishing or cmp or planarizing) and (etch or etching)) and semiconductor) and ((flow or flowing) with (etch or etching))) and backside) not plasma	USPAT	2003/09/20 12:33
14	0	6537416.URPN.	USPAT	2003/09/20 12:36
15	9	("4313266" | "4788994" | "5486234" | "5810940" | "5882433" | "6167893" | "6217034" | "6309981" | "6333275").PN.	USPAT	2003/09/20 12:36
17	331	((((polish or polishing or cmp or planarizing) and (etch or etching)) and semiconductor) and ((flow or flowing) with (etch or etching))) not plasma	USPAT	2003/09/20 12:38
18	259	(((((polish or polishing or cmp or planarizing) and (etch or etching)) and semiconductor) and ((flow or flowing) with (etch or etching))) not plasma) and @ay<=1999	USPAT	2003/09/20 12:39
19	5903	((((polish or polishing or cmp or planarizing) and (etch or etching)) and semiconductor) and (flow or flowing)) and (liquid or wet)	USPAT	2003/09/20 13:00
20	2367	(((((polish or polishing or cmp or planarizing) and (etch or etching)) and semiconductor) and (flow or flowing)) and (liquid or wet)) not plasma	USPAT	2003/09/20 13:00
21	2367	((((((polish or polishing or cmp or planarizing) and (etch or etching)) and semiconductor) and (flow or flowing)) and (liquid or wet)) not plasma) and (spray or spraying or flow or flowing)	USPAT	2003/09/20 13:01
22	2183	(((((((polish or polishing or cmp or planarizing) and (etch or etching)) and semiconductor) and (flow or flowing)) and (liquid or wet)) not plasma) and (spray or spraying or flow or flowing)) not (((((polish or polishing or cmp or planarizing) and (etch or etching)) and semiconductor) and ((flow or flowing) with (etch or etching))) not plasma)	USPAT	2003/09/20 13:01
23	1529	((((((((polish or polishing or cmp or planarizing) and (etch or etching)) and semiconductor) and (flow or flowing)) and (liquid or wet)) not plasma) and (spray or spraying or flow or flowing)) not (((((polish or polishing or cmp or planarizing) and (etch or etching)) and semiconductor) and ((flow or flowing) with (etch or etching))) not plasma)) and @ay<=1999	USPAT	2003/09/20 13:01

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24	723	((((((((((polish or polishing or cmp or planarizing) and (etch or etching)) and semiconductor) and (flow or flowing)) and (liquid or wet)) not plasma) and (spray or spraying or flow or flowing)) not (((((polish or polishing or cmp or planarizing) and (etch or etching)) and semiconductor) and ((flow or flowing) with (etch or etching))) not plasma)) and @ay<=1999) and edge	USPAT	2003/09/20 13:02
25	56	(((((((((((polish or polishing or cmp or planarizing) and (etch or etching)) and semiconductor) and (flow or flowing)) and (liquid or wet)) not plasma) and (spray or spraying or flow or flowing)) not (((((polish or polishing or cmp or planarizing) and (etch or etching)) and semiconductor) and ((flow or flowing) with (etch or etching))) not plasma)) and @ay<=1999) and edge) and (incline or inclining or inclined)	USPAT	2003/09/20 13:07
26	4	("2956494" | "3958587" | "5339842" | "6047715").PN.	USPAT	2003/09/20 13:04
27	123	438/745.ccls. and 438/692.ccls.	USPAT	2003/09/20 13:07
28	101	(438/745.ccls. and 438/692.ccls.) and @ay<=2000	USPAT	2003/09/20 13:12
29	1	5967156.pn.	USPAT	2003/09/20 13:15
30	9	5967156.URPN.	USPAT	2003/09/20 13:12
31	73	("1899626" | "2699403" | "3074822" | "3214867" | "3270464" | "3545996" | "3676963" | "3702519" | "3704822" | "3708993" | "3934374" | "3984943" | "4038786" | "4084357" | "4300581" | "4326553" | "4365383" | "4389820" | "4401131" | "4439243" | "4458703" | "4500080" | "4585517" | "4597825" | "4631250" | "4655847" | "4663890" | "4703590" | "4704873" | "4705438" | "4707951" | "4727687" | "4744181" | "4747421" | "4749440" | "4753051" | "4756047" | "4778559" | "4793103" | "4806171" | "4817652" | "4832753" | "4857142" | "4870923" | "4871651" | "4900395" | "4932168" | "4936922" | "4938815" | "4962891" | "4974375" | "5001873" | "5009240" | "5018667" | "5022961" | "5025597" | "5026155" | "5035750" | "5044129" | "5044314" | "5062898" | "5074083" | "5081068" | "5108512" | "5119637" | "5125979" | "5147466" | "5209028" | "5228206" | "5231865" | "5234540" | "5279705" | "5289263").PN.	USPAT	2003/09/20 13:13
32	2774	laminar and semiconductor	USPAT	2003/09/20 13:15
33	1785	(laminar and semiconductor) and (etch or etching or clean or cleaning)	USPAT	2003/09/20 13:16
34	1513	((laminar and semiconductor) and (etch or etching or clean or cleaning)) and @ay<=1999	USPAT	2003/09/20 13:16
35	846	(laminar and semiconductor) and ((etch or etching or clean or cleaning) same semiconductor)	USPAT	2003/09/20 13:16
36	713	((laminar and semiconductor) and ((etch or etching or clean or cleaning) same semiconductor)) and @ay<=1999	USPAT	2003/09/20 13:17

37	113	(((laminar and semiconductor) and ((etch or etching or clean or cleaning) same semiconductor)) and @ay<=1999) and (polish or polishing or cmp or planarize or planarizing)	USPAT	2003/09/20 13:17
38	689	(((laminar and semiconductor) and ((etch or etching or clean or cleaning) same semiconductor)) and @ay<=1999) not ink	USPAT	2003/09/20 13:17
39	461	((((laminar and semiconductor) and ((etch or etching or clean or cleaning) same semiconductor)) and @ay<=1999) not ink) not plasma	USPAT	2003/09/20 14:10
40	15	("4550684" | "4558660" | "4811493" | "4949783" | "5033407" | "5181556" | "5259883" | "5447431" | "5520538" | "5561735" | "5778968" | "5937541" | "5960158" | "5991508" | "6054684").PN.	USPAT	2003/09/20 13:22
41	2	5451267.pn. 6474644.pn.	USPAT	2003/09/20 14:10
42	2	5451267.pn. 5474644.pn.	USPAT	2003/09/20 14:11
43	0	"673545"	EPO	2003/09/20 14:16
44	0	"0673545"	EPO	2003/09/20 14:11
45	0	"0673545.pn."	EPO	2003/09/20 14:11
46	0	EP near "0673545"	EPO	2003/09/20 14:17
50	14636	((polish or polishing or cmp or planarizing) and (etch or etching)) not plasma	USPAT	2003/09/20 14:42
51	10371	(((polish or polishing or cmp or planarizing) and (etch or etching)) and semiconductor) not plasma	USPAT	2003/09/20 14:43
52	668	((((polish or polishing or cmp or planarizing) and (etch or etching)) and semiconductor) not plasma) and backside	USPAT	2003/09/20 14:43
53	373	((polish or polishing or cmp or planarizing) and (etch or etching)) and ((polish or polishing or cmp or planarizing) with (back$1side or (second adj side)))	USPAT	2003/09/20 14:44
54	258	(((polish or polishing or cmp or planarizing) and (etch or etching)) and ((polish or polishing or cmp or planarizing) with (back$1side or (second adj side)))) and @ay<=1999	USPAT	2003/09/20 14:56
55	1	5967156.pn.	USPAT	2003/09/20 14:56
–	2774	laminar and semiconductor	USPAT	2003/09/20 12:31
–	1854	(laminar with (flow or flowing)) and semiconductor	USPAT	2003/09/16 09:30
–	741	((laminar with (flow or flowing)) and semiconductor) and (etch or etching)	USPAT	2003/09/16 09:30
–	713	(((laminar with (flow or flowing)) and semiconductor) and (etch or etching)) and (laminar near3 (flow or flowing))	USPAT	2003/09/16 09:31
–	222	((((laminar with (flow or flowing)) and semiconductor) and (etch or etching)) and (laminar near3 (flow or flowing))) and (cmp or polish or polishing or polished or planarizitaion or planarize or planarizing)	USPAT	2003/09/16 09:32
–	209	(((((laminar with (flow or flowing)) and semiconductor) and (etch or etching)) and (laminar near3 (flow or flowing))) and (cmp or polish or polishing or polished or planarizitaion or planarize or planarizing)) and @ay<=2000	USPAT	2003/09/16 13:31

–	16056	laminar near3 (flow or flowing)	USPAT	2003/09/16 13:32
–	1765	(laminar near3 (flow or flowing)) and semiconductor	USPAT	2003/09/16 13:32
–	5168	laminar near3 (flow or flowing)	US-PGPUB; EPO; JPO	2003/09/16 13:32
–	669	(laminar near3 (flow or flowing)) and semiconductor	US-PGPUB; EPO; JPO	2003/09/16 13:33
–	291	((laminar near3 (flow or flowing)) and semiconductor) and (etch or etching)	US-PGPUB; EPO; JPO	2003/09/16 13:33
–	31	(((laminar near3 (flow or flowing)) and semiconductor) and (etch or etching)) and @ay<=2000	US-PGPUB; EPO; JPO	2003/09/16 14:46
–	1	5451267.pn.	USPAT	2003/09/16 14:46
–	10	5451267.URPN.	USPAT	2003/09/16 14:46